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## IN THE CLAIMS

Please substitute the following listing of claims for the previous listing of claims.

1. (Currently amended) A method of cleaning process residues from the a surface of a substrate processing chamber component having holes therein, the method comprising:

(a) at least partially immersing the component into a cleaning solution comprising hydrofluoric acid and nitric acid; and

(b) passing a non-reactive gas through the holes in the component, whereby the process residues are at least partially cleaned from the surface of the substrate processing chamber component.

2. (Original) A method according to claim 1 wherein the non-reactive gas is flowed through the holes at a pressure that is sufficiently high to prevent back flow of cleaning solution into the holes.

3. (Original) A method according to claim 1 wherein the non-reactive gas is flowed through the holes at a pressure of at least about 2 psi.

4. (Currently amended) A method according to claim 1 wherein the a flow rate of the non-reactive gas passing through the holes is at least about 100 sccm.

5. (Currently amended) A method according to claim 1 wherein the a concentration of hydrofluoric acid in the cleaning solution is at least about 1 percent.

6. (Currently amended) A method according to claim 1 wherein the a concentration of nitric acid in the cleaning solution is at least about 20 percent.

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7. (Currently amended) A method according to claim 1 wherein ~~in~~ the non-reactive gas is nitrogen.

8. (Original) A method according to claim 1 wherein the component is an electrostatic chuck, and the holes in the component are gas ports.

9. (Currently amended) A method of cleaning residues from the a surface of an electrostatic chuck having gas ports, the method comprising:

(a) at least partially immersing the electrostatic chuck into a cleaning solution comprising hydrofluoric acid in a concentration of at least about 1 percent and nitric acid in a concentration of at least about 20 percent; and

(b) flowing a non-reactive gas through the gas ports in the electrostatic chuck at a pressure of at least about 2 psi,

whereby the residues are at least partially cleaned from the surface of the electrostatic chuck.

10. (Currently amended) A method according to claim 9 wherein the a flow rate of the non-reactive gas passing through the gas ports is at least about 100 sccm.

11. (Currently amended) A method according to claim 9 wherein ~~in~~ the non-reactive gas is nitrogen.

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12. (Currently amended) A method of cleaning sputtering residues from the a surface of an electrostatic chuck having gas ports, the method comprising:

(a) at least partially immersing the electrostatic chuck into a cleaning solution comprising hydrofluoric acid in a concentration of at least about 1 percent and nitric acid in a concentration of at least about 20 percent; and

(b) flowing nitrogen through the gas ports in the electrostatic chuck at a pressure of at least about 2 psi and a flow rate of at least about 100 sccm,

whereby the sputtering residues are at least partially cleaned from the surface of the electrostatic chuck.

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